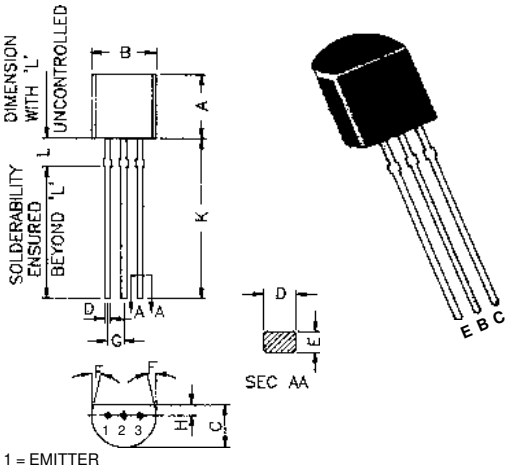
TO-92 Plastic Package

2N4400, 2N4401
2N4402, 2N4403

2N4400, 4401 NPN SILICON PLANAR EPITAXIAL TRANSISTORS
2N4402, 4403 PNP SILICON PLANAR EPITAXIAL TRANSISTORS
General Purpose Switching Applications



1 = EMITTER
2 = BASE
3 = COLLECTOR

DIM	MIN	MAX
A	4,32	5,33
B	4,45	5,20
C	3,18	4,19
D	0,41	0,55
E	0,35	0,50
F	5 DEG	
G	1,14	1,40
H	1,14	1,53
K	12,70	–
L	1.982	2.082

ALL DIMENSIONS IN M.M.

ABSOLUTE MAXIMM RATINGS

Rating	Symbol	2N4400/ 01	2N4402/ 03	Units
Collector-Emitter Voltage	V_{CEO}	40	40	V
Collector-Base Voltage	V_{CBO}	60	40	V
Emitter-Base Voltage	V_{EBO}	6	5	V
Collector Current Continuous	I_C	- 600	-	mA
Power Dissipation At Ta=25 °C	P_D	- 625	-	mW
Derate Above 25 °C		- 5.0	-	mW/ °C
Power Dissipation At Tc=25 °C	P_D	- 1.5	-	W
Derate Above 25 °C		- 12	-	mW/ °C
Operating & Storage Junction Temperature Range	T_j,T_{stg}	-55 to +150		°C

THERMAL RESISTANCE

Junction to Case	$R_{th\ (j\text{-}c)}$	- 83.3	-	°C/ W
Junction to Ambient	$R_{th\ (j\text{-}a)}$	- 200	-	°C/ W

ELECTRICAL CHARACTERISTICS *(Ta =25 °C unless otherwise specified)*

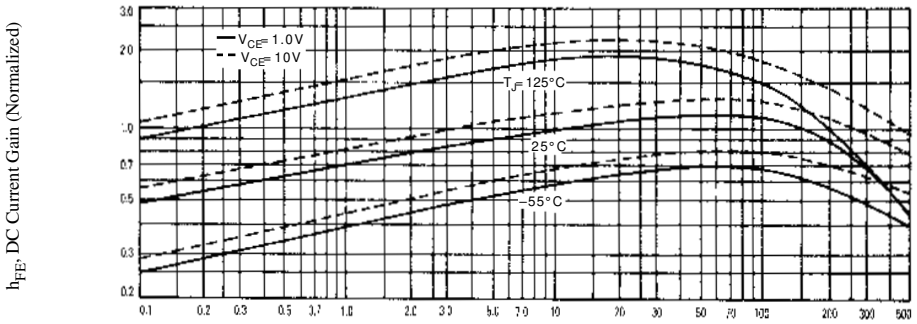
Characteristic	Symbol	2N4400/01	2N4402/03	Unit
Collector Emitter Voltage				
I_C=1mA, I_B=0	BV_{CEO}*	>40	>40	V
Collector Base Voltage				
I_C=100μA, I_E=0	BV_{CBO}	>60	>40	V
Emitter Base Voltage				
I_E=100μA, I_C=0	BV_{EBO}	>6	>5	V
Base Cutoff Current				
V_{CE}=35V, V_{BE}=0.4V	I_{BEV}	<0.1	<0.1	μA
Collector Cutoff Current				
V_{CE}=35V, V_{BE}=0.4V	I_{CEX}	<0.1	<0.1	μA
Collector-Emitter				
Saturation Voltage				
I_C=150mA, I_B=15mA	$V_{CE\ (sat)}$*	<0.4	<0.4	V
I_C=500mA, I_B=50mA		<0.75	<0.75	V
Base-Emitter				
Saturation Voltage				
I_C=150mA, I_B=15mA	$V_{BE\ (sat)}$*	0.75 to 0.95	0.75 to 0.95	V
I_C=500mA,I_B=50mA		<1.2	<1.3	V

Characteristic	Symbol	2N4400	2N4401	2N4402	2N4403	Unit
D C Current Gain						
I_C=0.1mA,V_{CE}=1V	h_{FE}	-	>20	-	>30	
I_C=1mA,V_{CE}=1V		>20	>40	>30	>60	
I_C=10mA,V_{CE}=1V		>40	>80	>50	>100	
I_C=150mA,V_{CE}=1V*		50-150	100-300	-	-	
I_C=150mA,V_{CE}=2V*		-	-	50-150	100-300	
I_C=500mA,V_{CE}=2V*		>20	>40	>20	>20	
DYNAMIC CHARACTERISTICS						
Small Signal Current Gain						
I_C=1mA, V_{CE}=10V, f=1KHz	h_{fe}	20-250	40-500	30-250	60-500	
Input Impedance						
I_C=1mA, V_{CE}=10V, f=1KHz	h_{ie}	0.5-7.5	1.0-15	0.75-7.5	1.5-15	KΩ

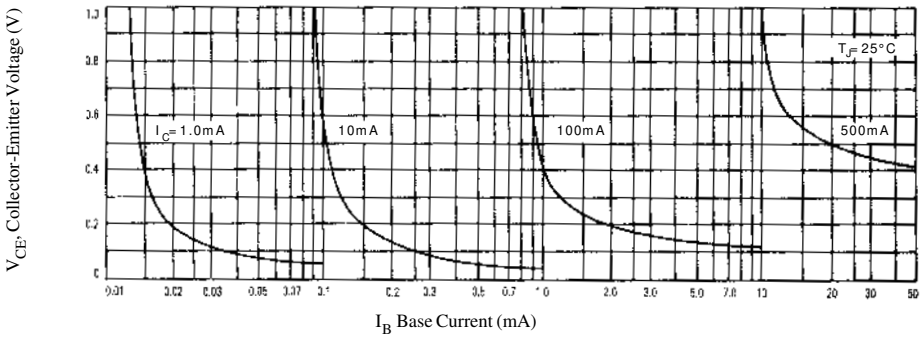
Characteristic	Symbol	2N4400	2N4401	2N4402	2N4403	Unit
Voltage Feedback Ratio I_C=1mA, V_{CE}=10V, f=1KHz	h_{re} **ALL**			0.1-8.0		$x10^{-4}$
Output Admittance I_C=1mA, V_{CE}=10V, f=1KHz	h_{oe}	1.0-30	1.0-30	1.0-100	1.0-100	μ℧
Collector-Base Capacitance V_{CB}=5V, I_E=0, f=100KHz	C_{cb}	<6.5	<6.5	-	-	pF
V_{CB}=10V, I_E=0, f=140KHz		-	-	<8.5	<8.5	pF
Emitter-Base Capacitance V_{EB}=0.5V, I_C=0, f=100KHz	C_{eb}	<30	<30	-	-	pF
V_{EB}=0.5V, I_C=0, f=140KHz		-	-	<30	<30	pF
Transition Frequency I_C=20mA, V_{CE}=10V f=100MHz	f_T	>200	>250	>150	>200	MHz
SWITCHING CHARACTERISTICS						
V_{CC}=30V, V_{EB}=2V, I_C=150mA, I_{B1}=15mA						
Delay time	t_d **ALL**			<15		ns
Rise time	t_r **ALL**			<20		ns
V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA						
Storage time	t_s **ALL**			<225		ns
Fall time	t_f **ALL**			<30		ns

**Pluse Test : Pluse width ≤ 300μs, duty ≤ 2.0%.*

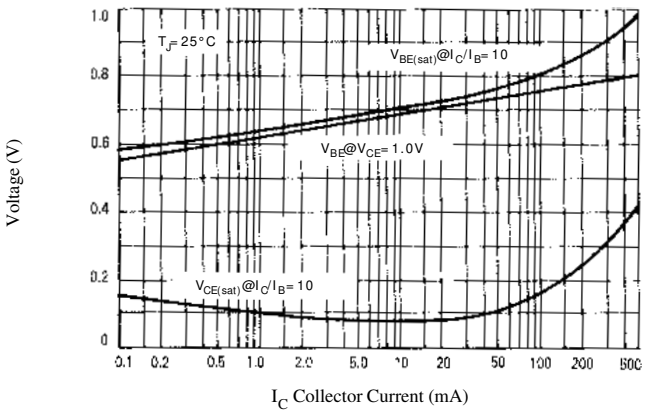
DC Current Gain



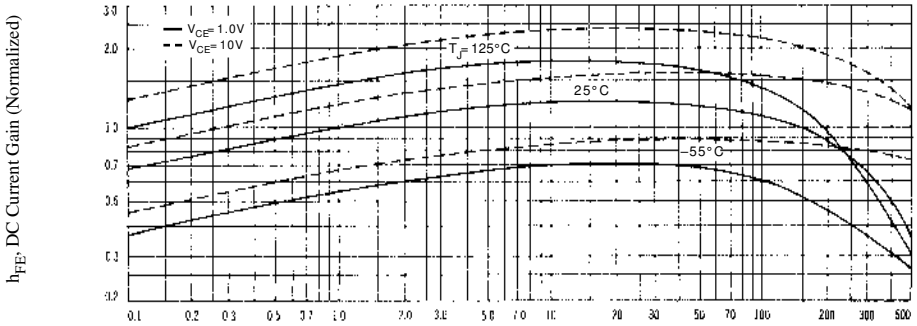
DC Current Gain



On Voltages



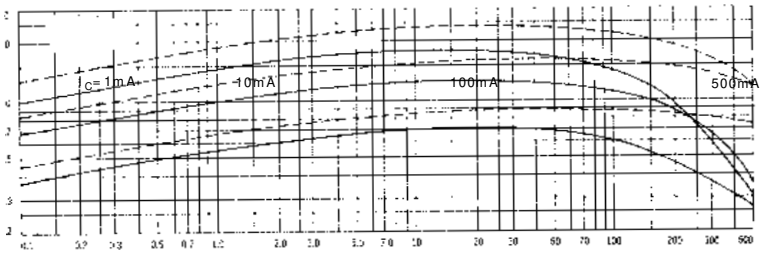
DC Current Gain



h_{FE}, DC Current Gain (Normalized)

I_C Collector Current (mA)

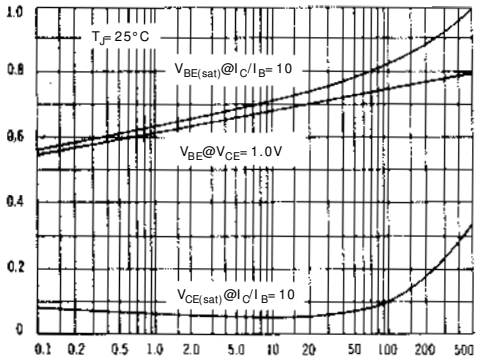
Collector Saturation Region



V_{CE} Collector-Emitter Voltage (V)

I_B Base Current (mA)

On Voltages



Voltage (V)

I_C Collector Current (mA)

Notes

Disclaimer

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